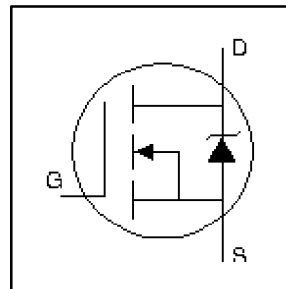


HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated



$$V_{DS} = 30V$$

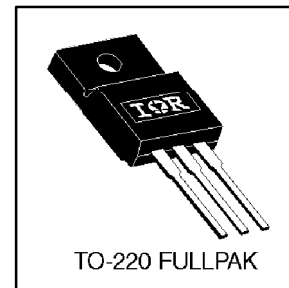
$$R_{DS(on)} = 0.026\Omega$$

$$I_D = 25A$$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	25	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	18	
I_{DM}	Pulsed Drain Current ①⑥	140	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	31	W
	Linear Derating Factor	0.21	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②⑥	130	mJ
I_{AR}	Avalanche Current ①⑥	20	A
E_{AR}	Repetitive Avalanche Current ①⑥	5.6	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑥	2.6	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	4.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	—	65	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⓐ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.026	Ω	$V_{GS} = 10V, I_D = 15A$ ⓐ
		—	—	0.040		$V_{GS} = 4.5V, I_D = 13A$ ⓐ
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	12	—	—	S	$V_{DS} = 25V, I_D = 20A$ ⓐ
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	26	nC	$I_D = 20A$
Q_{gs}	Gate-to-Source Charge	—	—	8.8		$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	15		$V_{GS} = 4.5V$, See Fig. 6 and 13 ⓐⓑ
$t_{d(on)}$	Turn-On Delay Time	—	7.4	—		$V_{DD} = 15V$
t_r	Rise Time	—	200	—	ns	$I_D = 20A$
$t_{d(off)}$	Turn-Off Delay Time	—	14	—		$R_G = 6.5\Omega, V_{GS} = 4.5V$
t_f	Fall Time	—	36	—		$R_D = 0.70\Omega$, See Fig. 10 ⓐⓑ
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	870	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	340	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	170	—		$f = 1.0\text{MHz}$, See Fig. 5ⓐ
C	Drain to Sink Capacitance	—	12	—		$f = 1.0\text{MHz}$



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	25	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ⓐⓑ	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 15A, V_{GS} = 0V$ ⓐ
t_{rr}	Reverse Recovery Time	—	72	110	ns	$T_J = 25^\circ\text{C}, I_F = 20A$
Q_{rr}	Reverse Recovery Charge	—	180	280	nC	$di/dt = 100A/\mu s$ ⓐⓑ

Notes:

- ⓐ Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ⓑ $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 470\mu H$
 $R_G = 25\Omega, I_{AS} = 20A$. (See Figure 12)
- ⓒ $I_{SD} \leq 20A, di/dt \leq 140A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ⓓ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⓔ $t = 60s, f = 60\text{Hz}$
- ⓕ Uses IRL3303 data and test conditions

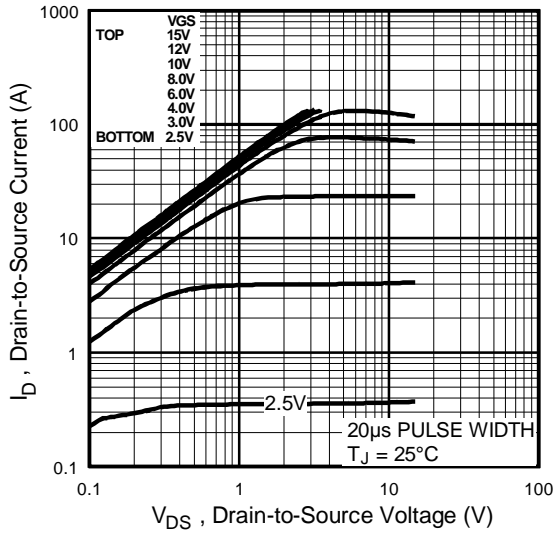


Fig 1. Typical Output Characteristics,
 $T_J = 25^\circ\text{C}$

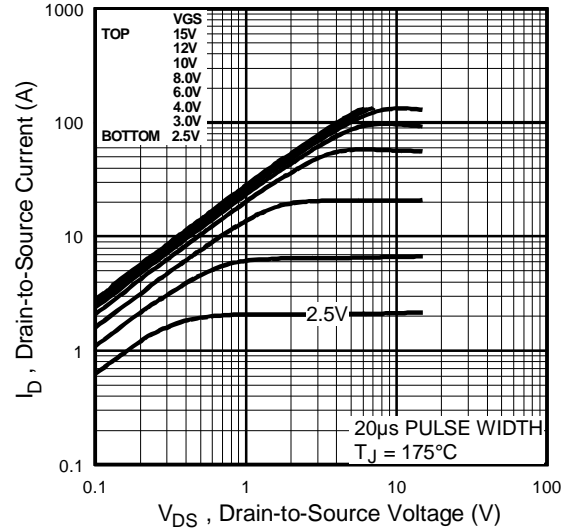


Fig 2. Typical Output Characteristics,
 $T_J = 175^\circ\text{C}$

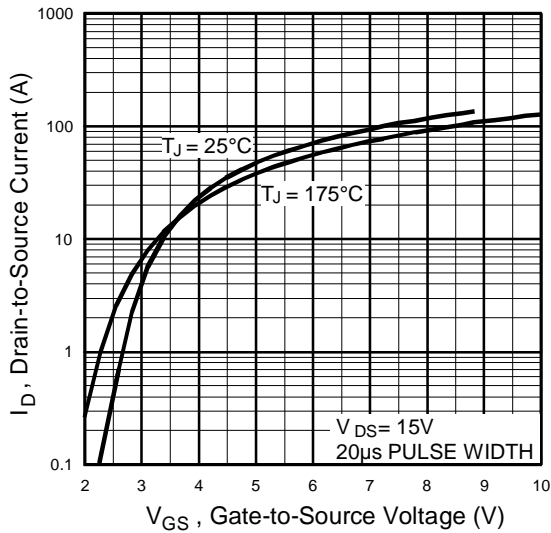


Fig 3. Typical Transfer Characteristics

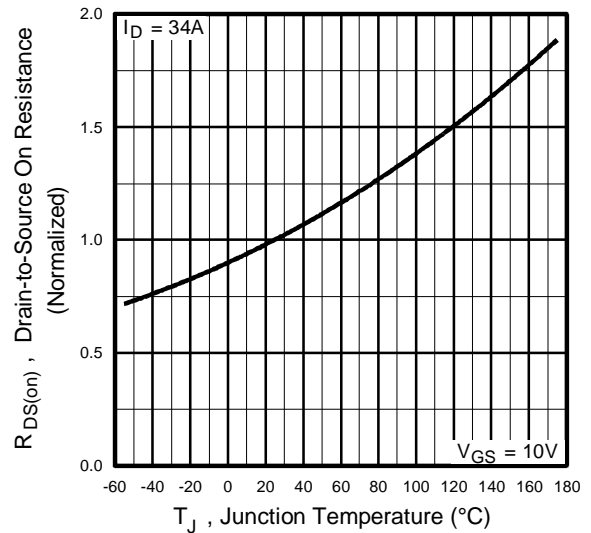


Fig 4. Normalized On-Resistance
Vs. Temperature

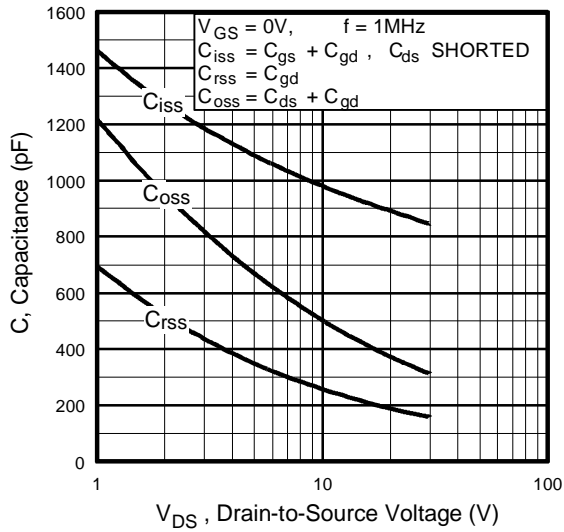


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

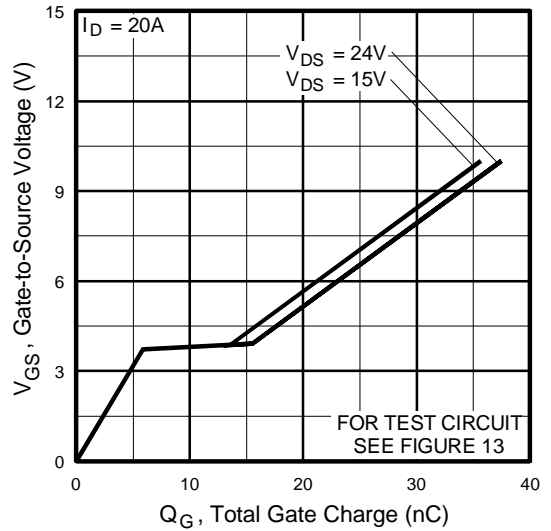


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

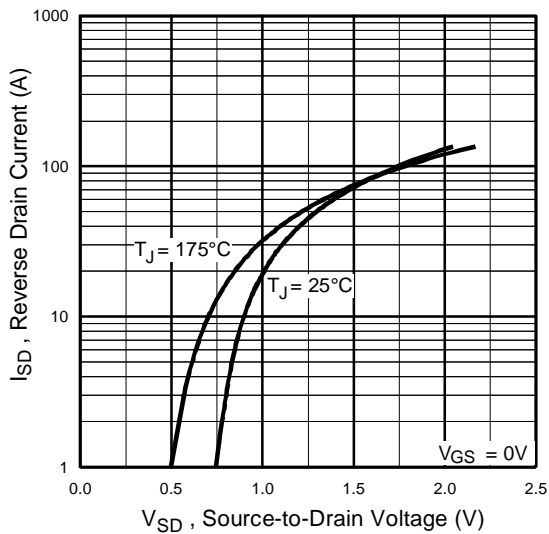


Fig 7. Typical Source-Drain Diode Forward Voltage

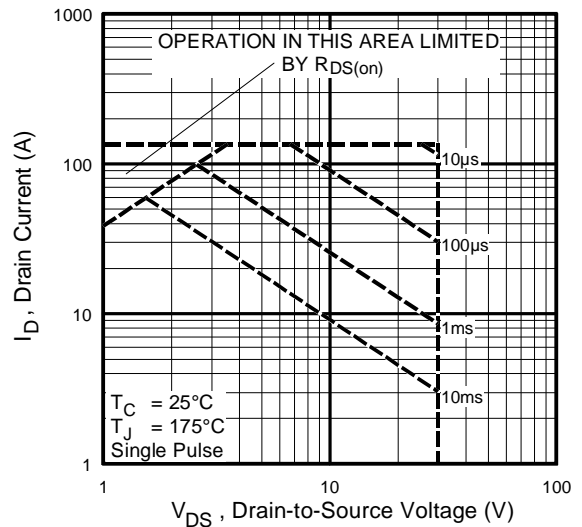


Fig 8. Maximum Safe Operating Area

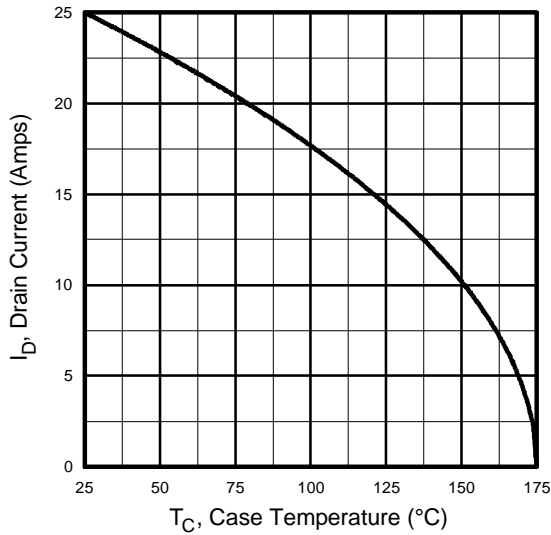


Fig 9. Maximum Drain Current Vs. Case Temperature

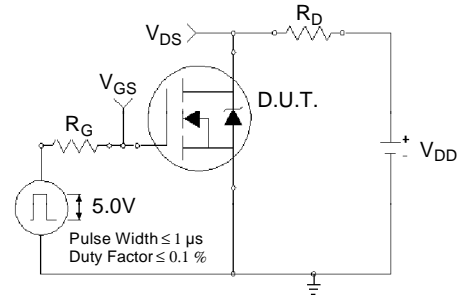


Fig 10a. Switching Time Test Circuit

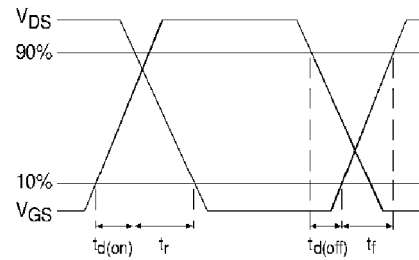


Fig 10b. Switching Time Waveforms

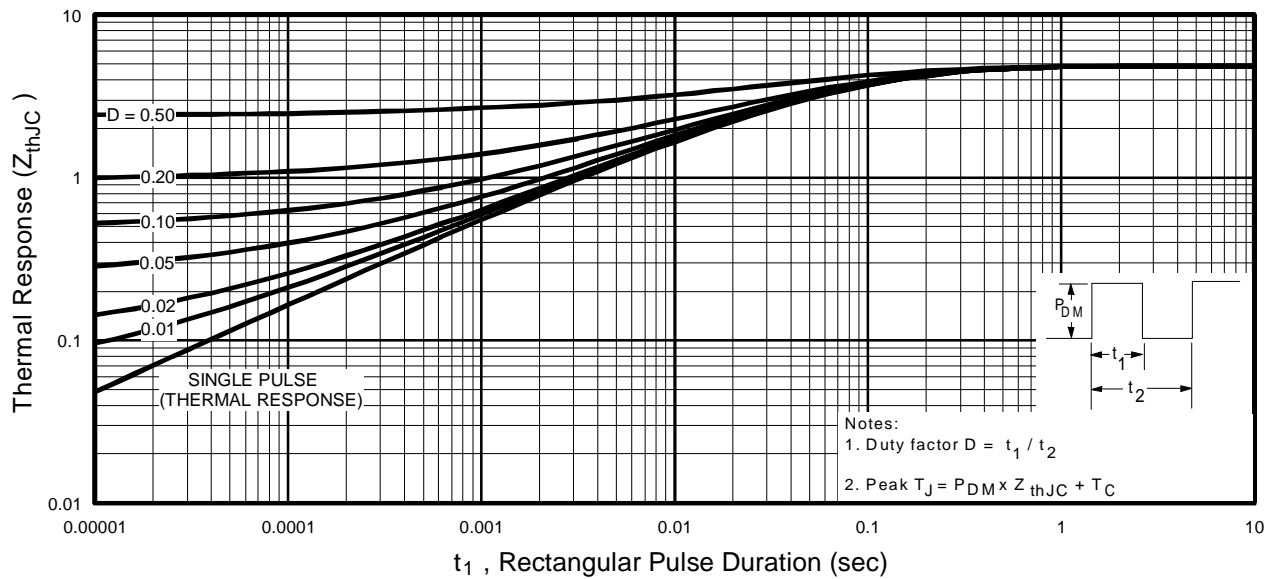


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

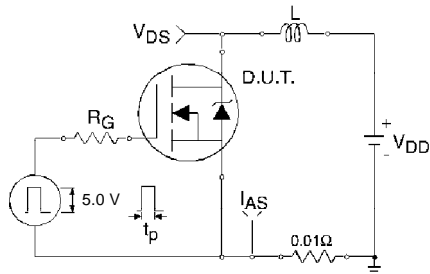


Fig 12a. Unclamped Inductive Test Circuit

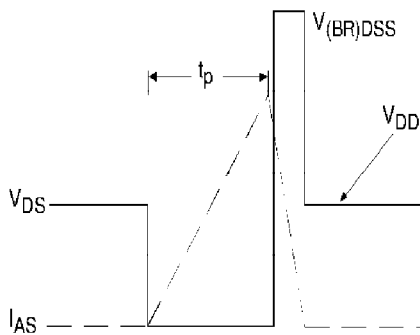


Fig 12b. Unclamped Inductive Waveforms

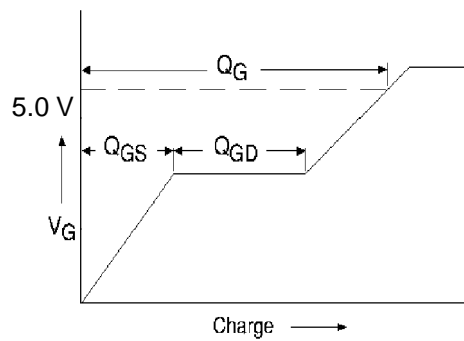


Fig 13a. Basic Gate Charge Waveform

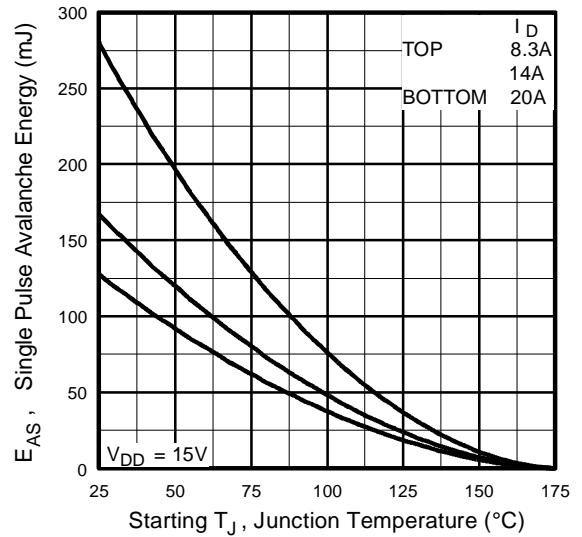


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

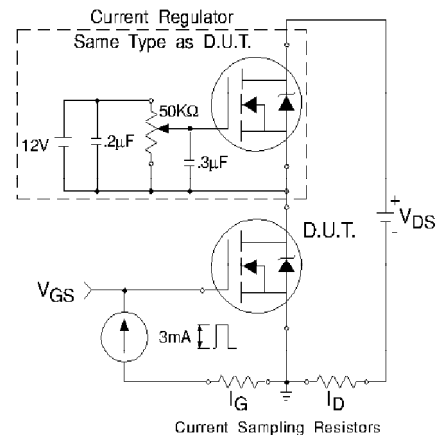
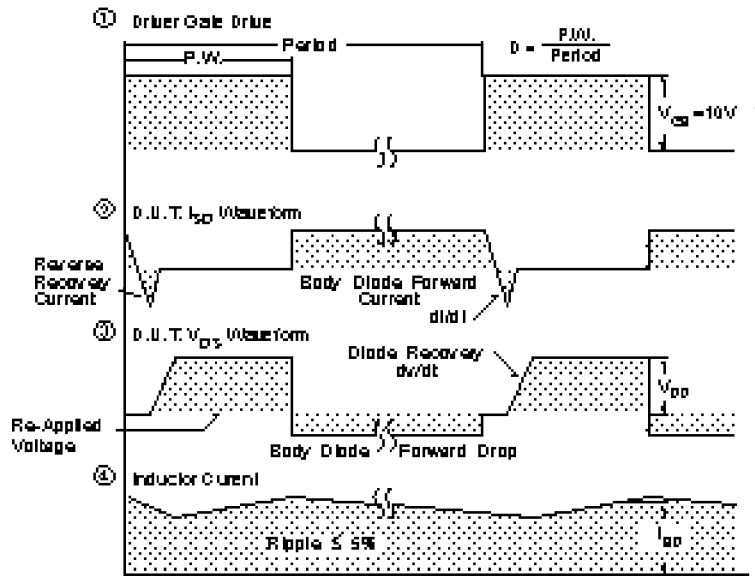
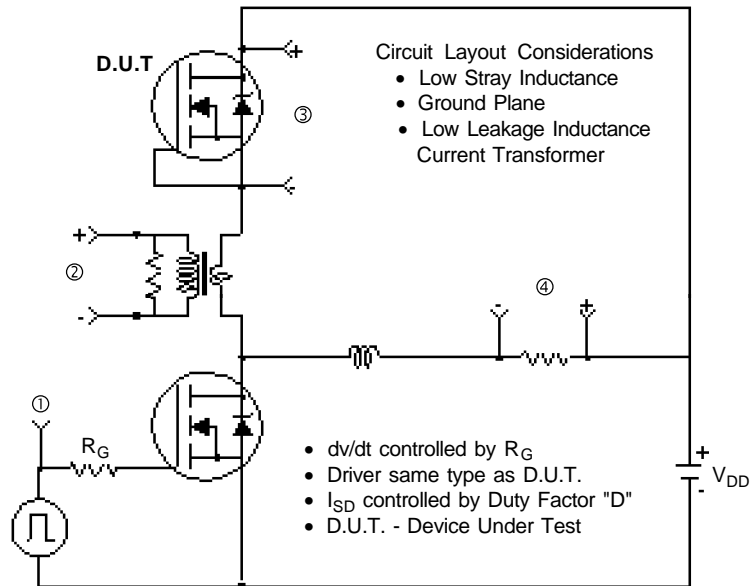


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

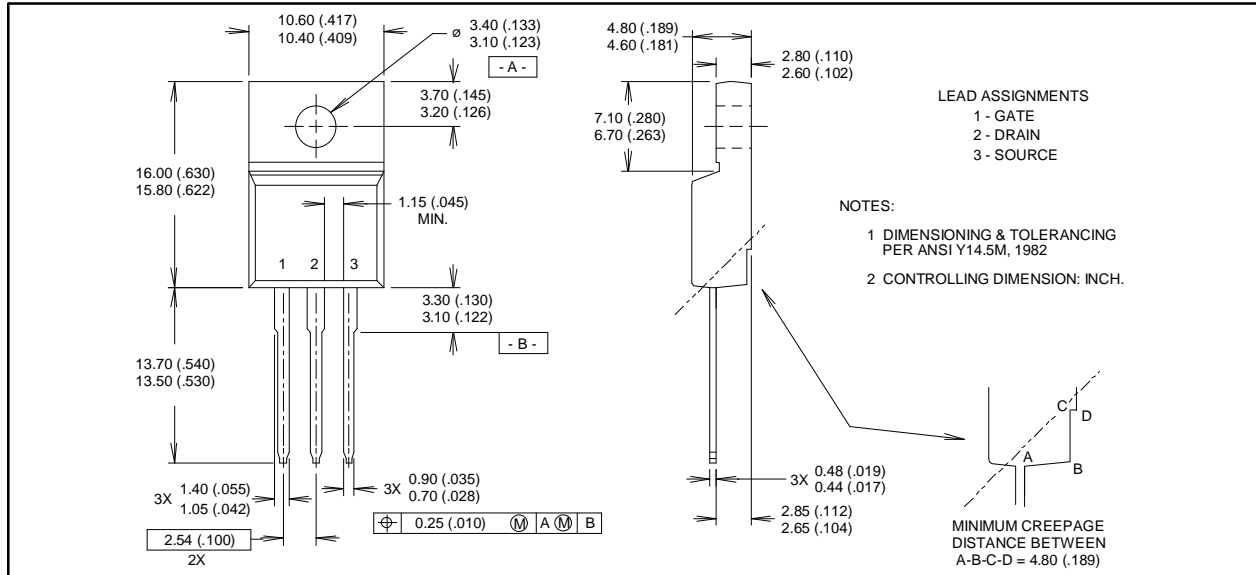
IRLI3303



Package Outline

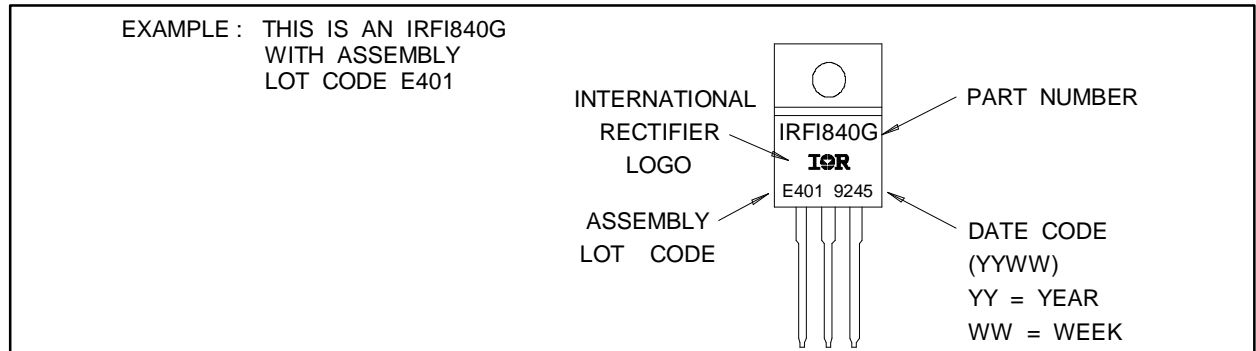
TO-220 FullPak Outline

Dimensions are shown in millimeters (inches)



Part Marking Information

TO-220 FullPak



WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331
EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: (44) 0883 713215
IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 3L1, Tel: (905) 475 1897
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: 6172 37066
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: (39) 1145 10111
IR FAR EAST: K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Chome, Toshima-Ki, Tokyo 171 Tel: (03)3983 0641
IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, 0316 Tel: 65 221 8371

Data and specifications subject to change without notice.